

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- Non Punch Through Silicon
- Isolated MMC Base with AlN Substrates

APPLICATIONS

- Inverters
- Motor Controllers
- Traction Drives

The Powerline range of modules includes half bridge, dual, chopper, bi-directional and single switch configurations covering voltages from 600V to 3300V and currents up to 2400A.

The DIM800DCM12-A000 is a 1200V, n channel enhancement mode insulated gate bipolar transistor (IGBT) chopper module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus full 10µs short circuit withstand. This module is optimised for applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM800DCM12-A000

Note: When ordering, please use the whole part number.

KEY PARAMETERS

V_{CES}		1200V
$V_{CE(sat)}$ *	(typ)	2.2V
I_C	(max)	800A
$I_{C(PK)}$	(max)	1600A

*(measured at the power busbars and not the auxiliary terminals)

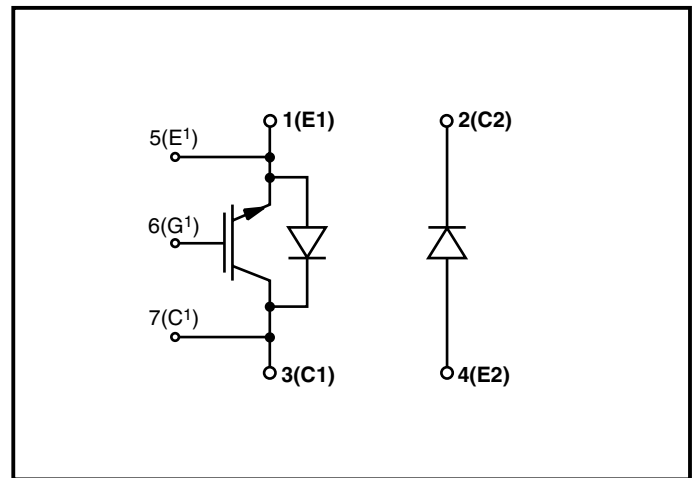


Fig. 1 Chopper circuit diagram

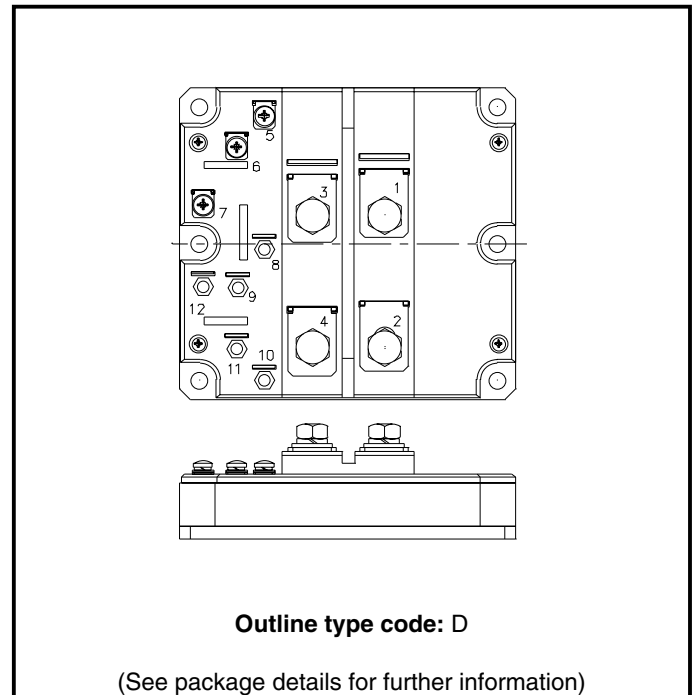


Fig. 2 Electrical connections - (not to scale)

ABSOLUTE MAXIMUM RATINGS - PER ARM

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0\text{V}$	1200	V
V_{GES}	Gate-emitter voltage	-	± 20	V
I_C	Continuous collector current	$T_{case} = 85^{\circ}\text{C}$	800	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 115^{\circ}\text{C}$	1600	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	6940	W
I^2t	Diode I^2t value (IGBT arm)	$V_R = 0$, $t_p = 10\text{ms}$, $T_{vj} = 125^{\circ}\text{C}$	100	kA^2s
	Diode I^2t value (Diode arm)		225	kA^2s
V_{isol}	Isolation voltage - per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V
Q_{PD}	Partial discharge - per module	IEC1287. $V_1 = 1800\text{V}$, $V_2 = 1300\text{V}$, 50Hz RMS	10	PC

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AlN
 Baseplate material: AISiC
 Creepage distance: 20mm
 Clearance: 10mm
 CTI (Critical Tracking Index): 175

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - transistor (per arm)	Continuous dissipation - junction to case	-	-	18	°C/kW
$R_{th(j-c)}$	Thermal resistance - diode (IGBT arm)	Continuous dissipation - junction to case	-	-	40	°C/kW
	Thermal resistance - diode (Diode arm)	junction to case	-	-	26.7	°C/kW
$R_{th(c-h)}$	Thermal resistance - case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	°C/kW
T_j	Junction temperature	Transistor	-	-	150	°C
		Diode	-	-	125	°C
T_{stg}	Storage temperature range	-	-40	-	125	°C
-	Screw torque	Mounting - M6	-	-	5	Nm
		Electrical connections - M4	-	-	2	Nm
		Electrical connections - M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = V _{CES}	-	-	1	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125°C	-	-	25	mA
I _{GES}	Gate leakage current	V _{GE} = ±20V, V _{CE} = 0V	-	-	4	µA
V _{GE(TH)}	Gate threshold voltage	I _C = 40mA, V _{GE} = V _{CE}	4.5	5.5	6.5	V
V _{CE(sat)} [†]	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 800A	-	2.2	2.8	V
		V _{GE} = 15V, I _C = 800A, T _{case} = 125°C	-	2.6	3.2	V
I _F	Diode forward current	DC	-	-	800	A
I _{FM}	Diode maximum forward current	t _p = 1ms	-	-	1600	A
V _F [†]	Diode forward voltage (IGBT arm)	I _F = 800A	-	2.1	2.4	V
	Diode forward voltage (Diode arm)		-	1.8	2.1	V
	Diode forward voltage (IGBT arm)	I _F = 800A, T _{case} = 125°C	-	2.1	2.4	V
	Diode forward voltage (Diode arm)		-	1.7	2.0	V
C _{ies}	Input capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	-	90	-	nF
L _M	Module inductance - per arm	-	-	20	-	nH
R _{INT}	Internal transistor resistance - per arm	-	-	0.27	-	mΩ
SC _{Data}	Short circuit. I _{SC}	T _j = 125°C, V _{CC} = 900V, t _p ≤ 10µs, V _{CE(max)} = V _{CES} - L* · di/dt IEC 60747-9	I ₁	5500	-	A
			I ₂	4500	-	A

Note:

† Measured at the power busbars and not the auxiliary terminals)

* L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS
T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
t _{d(off)}	Turn-off delay time	$I_C = 800A$ $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $R_{G(ON)} = R_{G(OFF)} = 2.7\Omega$ $L \sim 100nH$	-	1250	-	ns
t _f	Fall time		-	170	-	ns
E _{OFF}	Turn-off energy loss		-	130	-	mJ
t _{d(on)}	Turn-on delay time		-	250	-	ns
t _r	Rise time		-	250	-	ns
E _{ON}	Turn-on energy loss		-	80	-	mJ
Q _g	Gate charge		-	9	-	μC
Q _{rr}	Diode reverse recovery charge	$I_F = 800A, V_R = 600V,$ $di_F/dt = 4200A/\mu s$	-	80	-	μC
I _{rr}	Diode reverse current		-	380	-	A
E _{REC}	Diode reverse recovery energy		-	30	-	mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
t _{d(off)}	Turn-off delay time	$I_C = 800A$ $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $R_{G(ON)} = R_{G(OFF)} = 2.7\Omega$ $L \sim 100nH$	-	1500	-	ns
t _f	Fall time		-	200	-	ns
E _{OFF}	Turn-off energy loss		-	160	-	mJ
t _{d(on)}	Turn-on delay time		-	400	-	ns
t _r	Rise time		-	220	-	ns
E _{ON}	Turn-on energy loss		-	120	-	mJ
Q _{rr}	Diode reverse recovery charge		$I_F = 800A, V_R = 600V,$ $di_F/dt = 4000A/\mu s$	-	160	-
I _{rr}	Diode reverse current	-		450	-	A
E _{REC}	Diode reverse recovery energy	-		60	-	mJ

TYPICAL CHARACTERISTICS

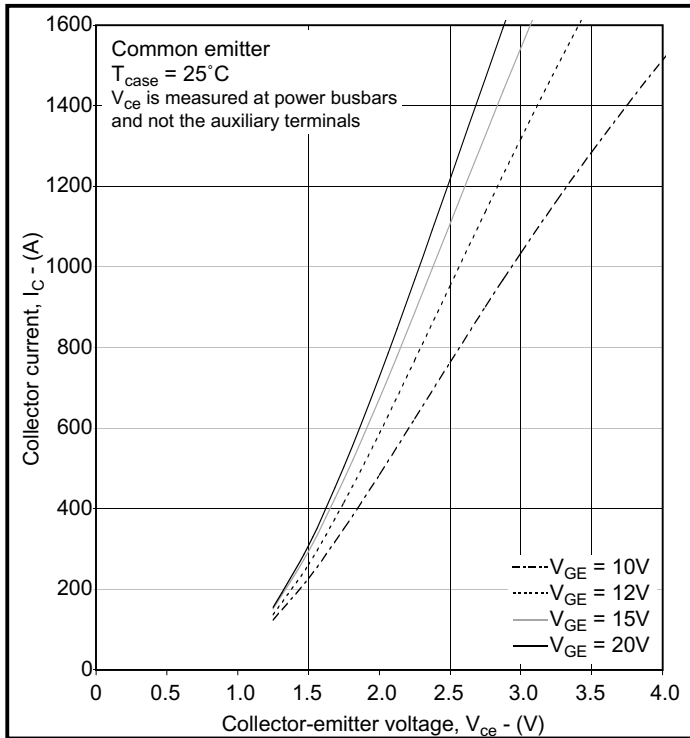


Fig. 3 Typical output characteristics

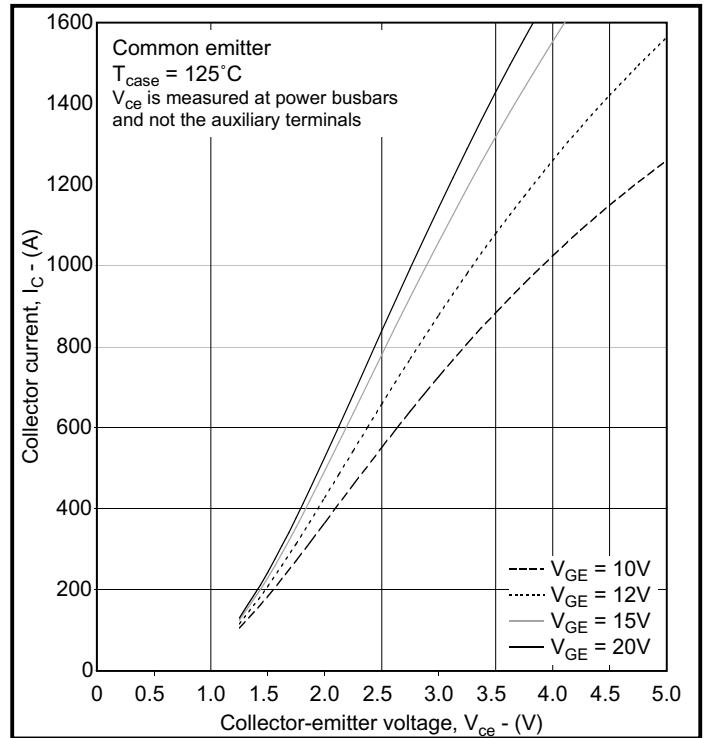


Fig. 4 Typical output characteristics

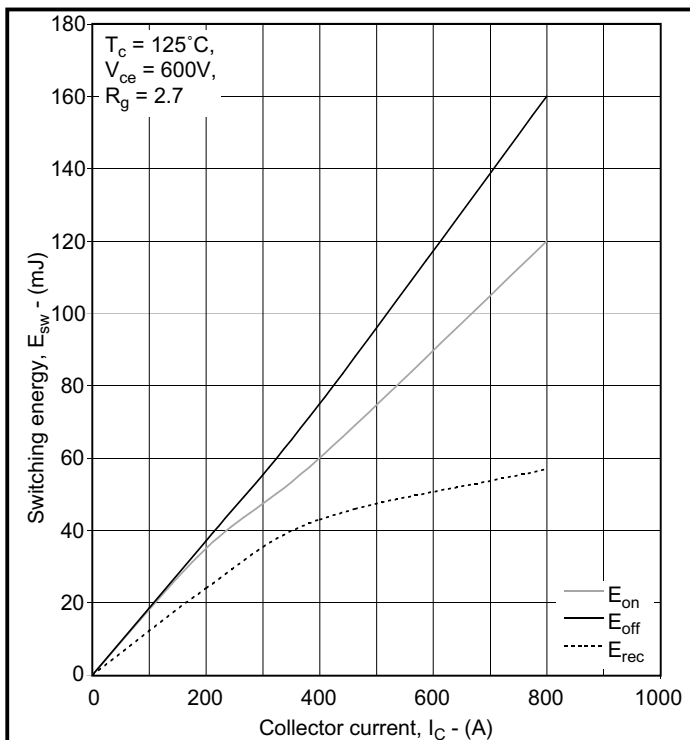


Fig. 5 Typical switching energy vs collector current

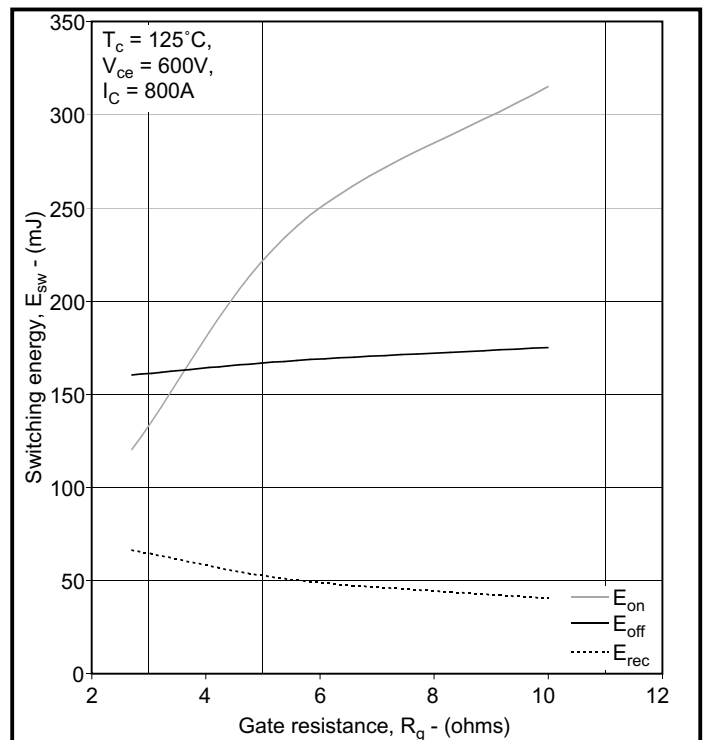


Fig. 6 Typical switching energy vs gate resistance

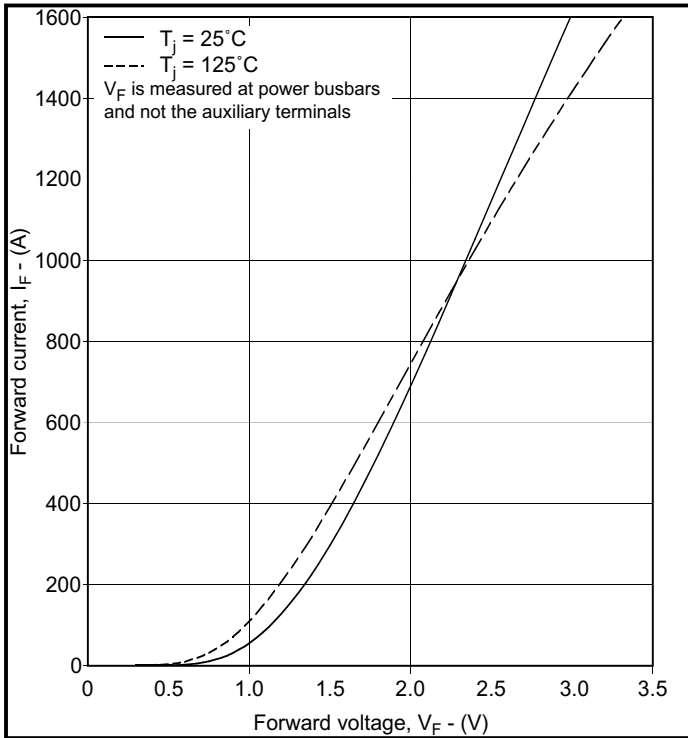


Fig. 7 Diode typical forward characteristics

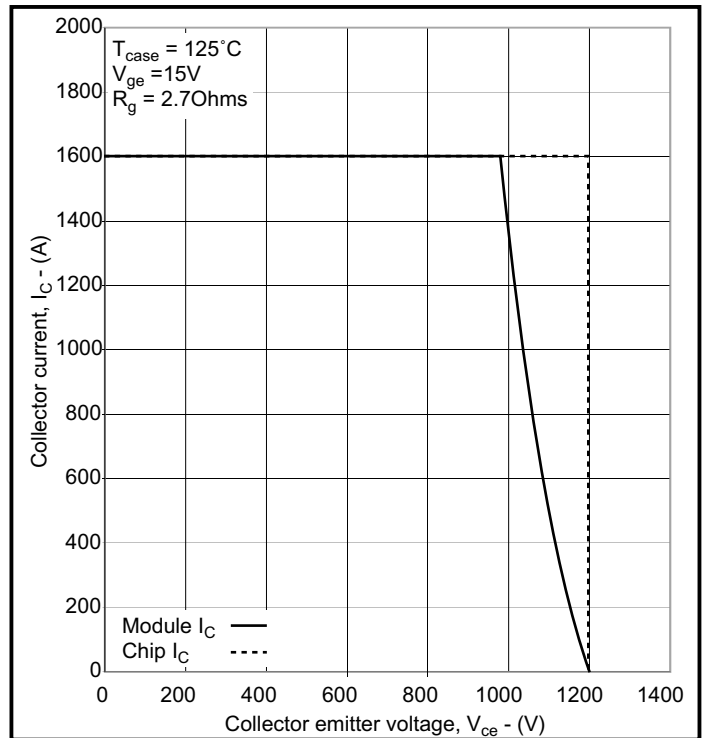


Fig. 8 Reverse bias safe operating area

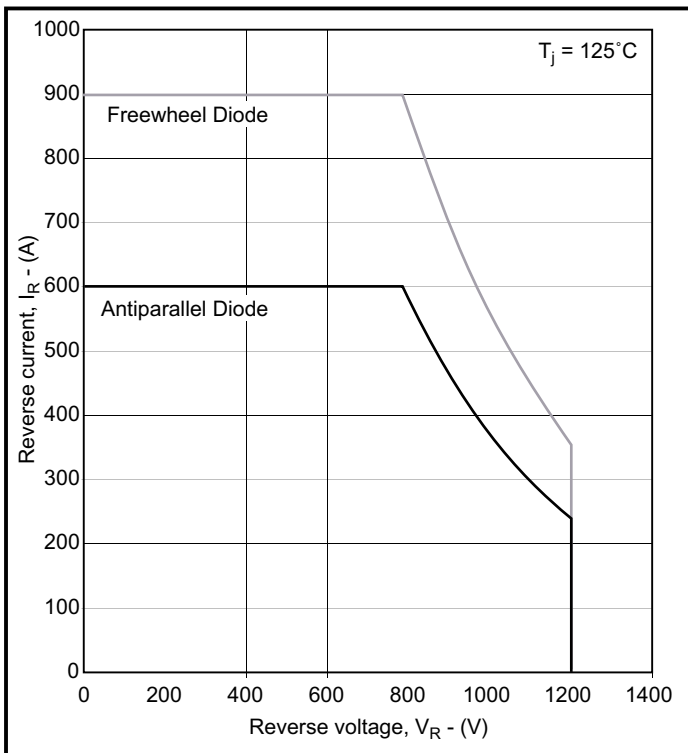


Fig. 9 Diode reverse bias safe operating area

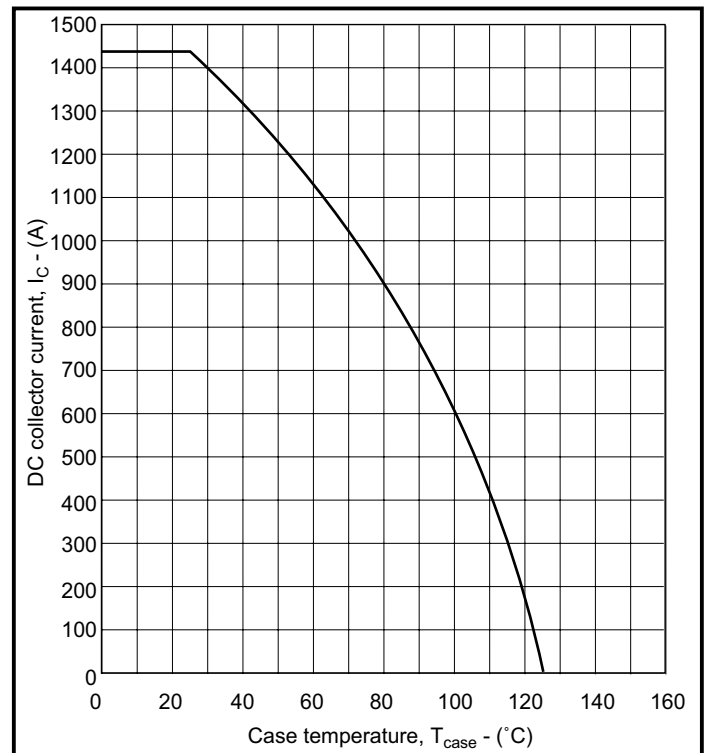


Fig. 10 DC current rating vs case temperature

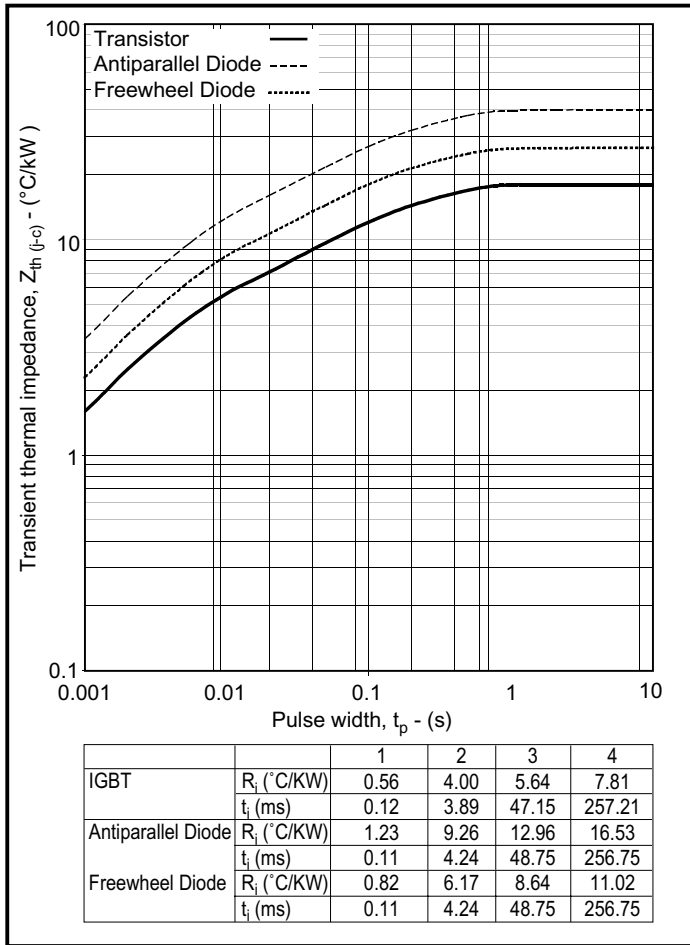
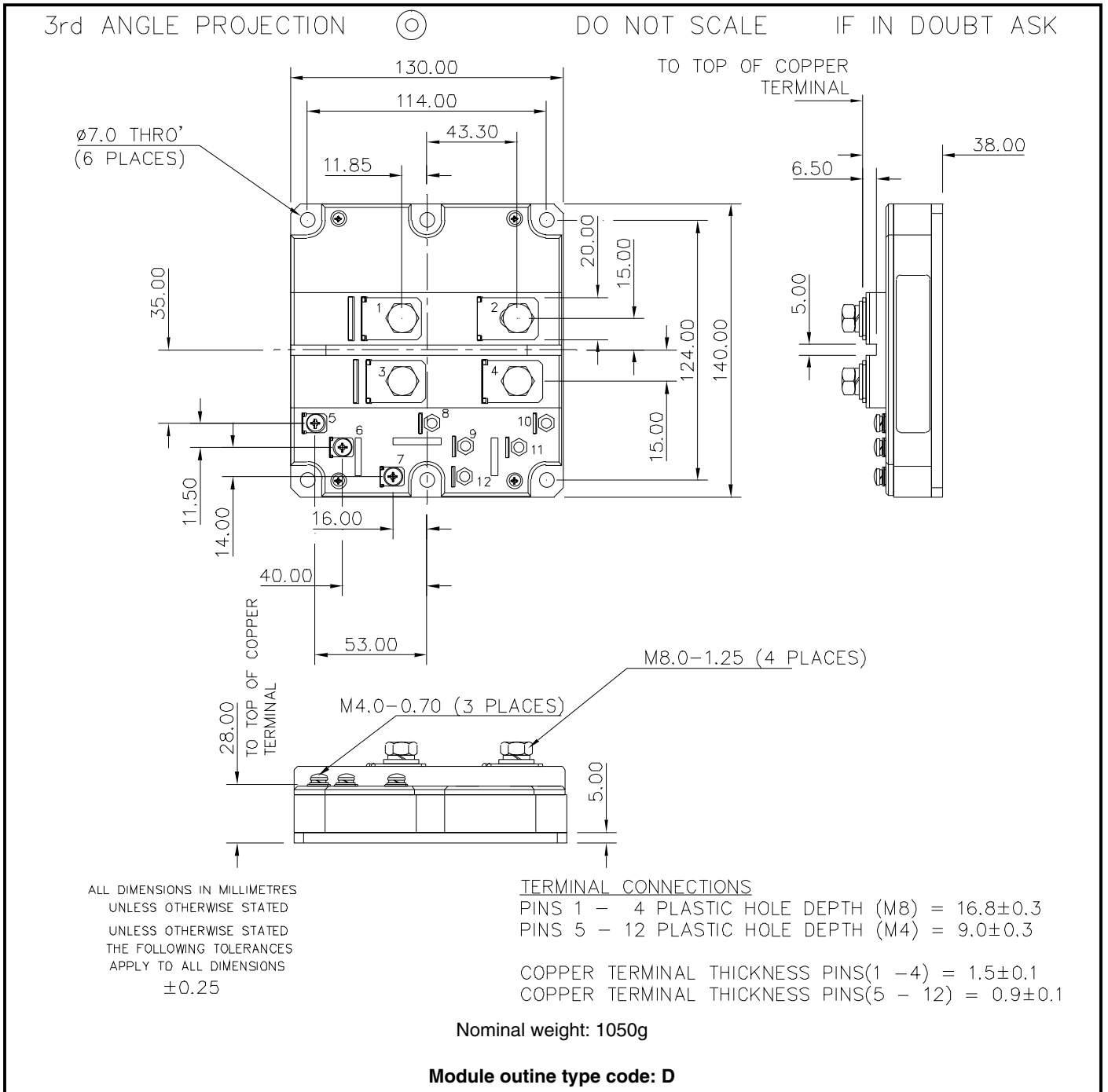


Fig. 11 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



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